imall

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Fast Switching Emitter Controlled Diode





Green

Feature

- 600V Emitter Controlled technology
- Fast recovery
- Soft switching
- Low reverse recovery charge
- Low forward voltage
- 175°C operating temperature
- Easy paralleling
- Qualified according to JEDEC⁰⁾ for target applications
- * RoHS compliant

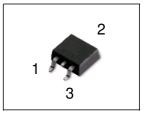
Туре	Package	Ordering Code	Marking	Pin 1	PIN 2	PIN 3
IDB45E60	PG-TO263-3	-	D45E60	NC	С	А

Maximum Ratings, at $T_i = 25$ °C, unless otherwise specified

Parameter	Symbol	Value	Unit	
Repetitive peak reverse voltage	V _{RRM}	600	V	
Continuous forward current				
$T_{\rm C} = 25^{\circ}{\rm C}$	I _F	71	А	
$T_{\rm C} = 90^{\circ}{\rm C}$		47		
Surge non repetitive forward current	1	162	A	
$T_{\rm C}$ = 25°C, $t_{\rm p}$ = 10 ms, sine halfwave	I _{FSM}	102		
Maximum repetitive forward current	1	111.5	A	
$T_{\rm C}$ = 25°C, $t_{\rm p}$ limited by $t_{\rm j,max}$, D = 0.5	/ _{FRM}	111.5		
Power dissipation				
$T_{\rm C} = 25^{\circ}{\rm C}$	P _{tot}	187	W	
$T_{\rm C} = 90^{\circ}{\rm C}$		106		
Operating junction temperature	Tj	-40+175		
Storage temperature	T _{stg}	-55+150	_∘C	
Soldering temperature	Ts	260	Ĵ	
1.6mm (0.063 in.) from case for 10 s	. 3	200		

Product Summary

	-	
V _{RRM}	600	V
/ _F	45	А
V _F	1.5	V
T _{jmax}	175	°C



PG-TO263-3



Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Characteristics					
Thermal resistance, junction - case	R _{thJC}	-	-	0.8	K/W
Thermal resistance, junction - ambient, leaded	R _{thJA}	-	-	62	
SMD version, device on PCB:	R _{thJA}				
@ min. footprint		-	-	62	
@ 6 cm ² cooling area ¹⁾		-	35	-	

Electrical Characteristics, at T_i = 25 °C, unless otherwise specified

Parameter	Symbol		Values		
		min.	typ.	max.	
Static Characteristics		-			
Reverse leakage current	/ _R				μA
V _R =600V, <i>T</i> _j =25°C		-	-	50	
V _R =600V, <i>T</i> _j =150°C		-	-	3000	
Forward voltage drop	V _F				V
I _F =45Α, <i>T</i> _j =25°C		-	1.5	2	
I _F =45A, T _j =25°C I _F =45A, T _j =150°C		-	1.5	-	

⁰J-STD20 and JESD22

¹Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70 µm thick) copper area for drain connection. PCB is vertical without blown air.



Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Dynamic Characteristics					
Reverse recovery time	t _{rr}				ns
V _R =400V, <i>I</i> _F =45A, d <i>i</i> _F /d <i>t</i> =1000A/μs, <i>T</i> _j =25°C		-	140	-	
V _R =400V, <i>I</i> _F =45A, d <i>i</i> _F /d <i>t</i> =1000A/μs, <i>T</i> _j =125°C		-	185	-	
<i>V</i> _R =400V, <i>I</i> _F =45A, d <i>i</i> _F /d <i>t</i> =1000A/μs, <i>T</i> _j =150°C		-	195	-	
Peak reverse current	I _{rrm}				A
V _R =400V, <i>I</i> _F = 45A, d <i>i</i> _F /d <i>t</i> =1000A/μs, <i>T</i> _j =25°C		-	23	-	
$V_{\rm R}$ =400V, $I_{\rm F}$ =45A, $d_{i\rm F}/dt$ =1000A/µs, T_{j} =125°C		-	28.1	-	
V _R =400V, <i>I</i> _F =45A, d <i>i</i> _F /d <i>t</i> =1000A/μs, <i>T</i> _j =150°C		-	29	-	
Reverse recovery charge	Q _{rr}				nC
V _R =400V, <i>I</i> _F =45A, d <i>i</i> _F /d <i>t</i> =1000A/μs, <i>T</i> _j =25°C		-	1400	-	
V _R =400V, <i>I</i> _F =45A, d <i>i</i> _F /d <i>t</i> =1000A/μs, <i>T</i> _j =125°C		-	2650	-	
$V_{\rm R}$ =400V, $I_{\rm F}$ =45A, $di_{\rm F}/dt$ =1000A/µs, $T_{\rm j}$ =150°C		-	2900	-	
Reverse recovery softness factor	S				
V _R =400V, / _F =45A, d <i>i</i> _F /d <i>t</i> =1000A/μs, 7 _j =25°C		-	3.1	-	
V _R =400V, <i>I</i> _F =45A, d <i>i</i> _F /d <i>t</i> =1000A/μs, <i>T</i> _j =125°C		-	4.2	-	
V _R =400V, <i>I</i> _F =45A, d <i>i</i> _F /d <i>t</i> =1000A/μs, <i>T</i> _i =150°C		-	4.4	-	

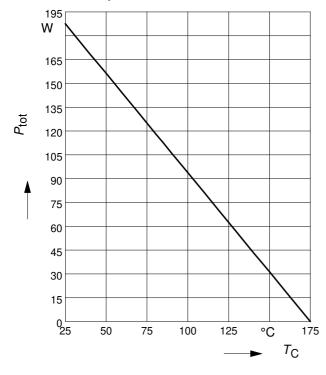
Electrical Characteristics, at $T_i = 25$ °C, unless otherwise specified

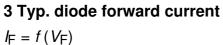


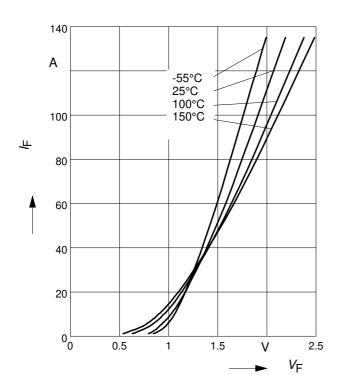
1 Power dissipation

 $P_{\text{tot}} = f(T_{\text{C}})$

parameter: $T_{j} \le 175 \text{ °C}$

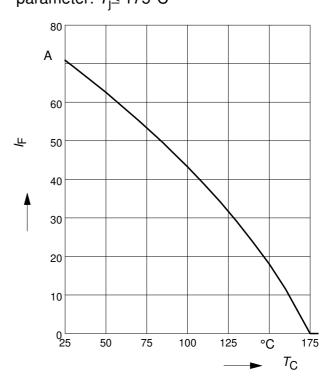




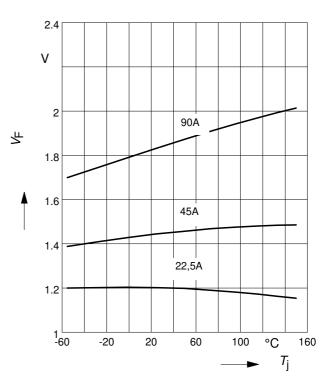


2 Diode forward current

 $I_{\rm F} = f(T_{\rm C})$ parameter: $T_{\rm j} \le 175^{\circ}{\rm C}$



4 Typ. diode forward voltage $V_{\mathsf{F}} = f(T_{\mathsf{j}})$



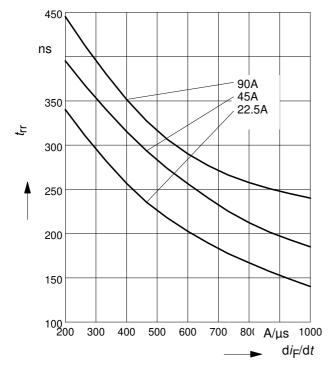
Rev.2.4



5 Typ. reverse recovery time

 $t_{\rm rr} = f \left({\rm d}i_{\rm F} / {\rm d}t \right)$

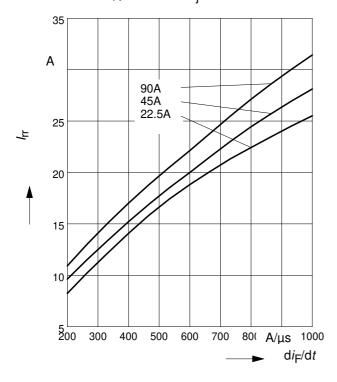
parameter: $V_{\rm R}$ = 400V, $T_{\rm j}$ = 125°C



7 Typ. reverse recovery current

 $I_{\rm rr} = f \left({\rm d}i_{\rm F}/{\rm d}t \right)$

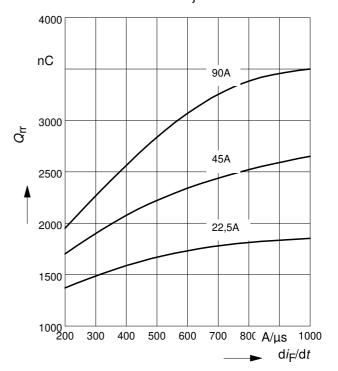
parameter: $V_{\text{R}} = 400\text{V}$, $T_{\text{i}} = 125^{\circ}\text{C}$



6 Typ. reverse recovery charge

 $Q_{\rm rr} = f(di_{\rm F}/dt)$

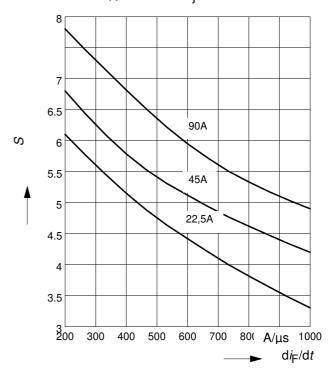
parameter: $V_{\rm R}$ = 400V, $T_{\rm i}$ = 125 °C



8 Typ. reverse recovery softness factor

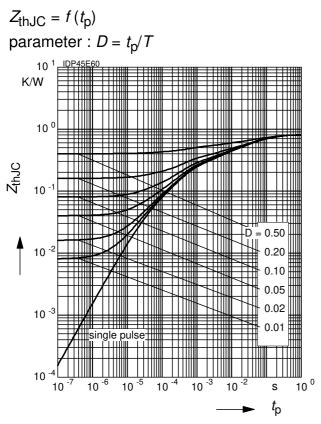
 $S = f(d_{F}/dt)$

parameter: $V_{R} = 400V$, $T_{i} = 125^{\circ}C$

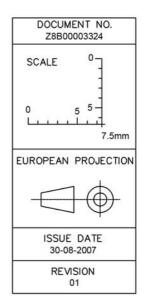


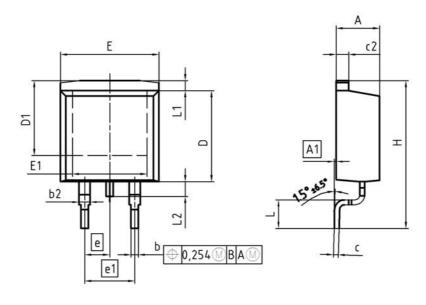


9 Max. transient thermal impedance



DIM	MILLIM	ETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
А	4.30	4.57	0.169	0.180	
A1	0.00	0.25	0.000	0.010	
b	0.65	0.85	0.026	0.033	
b2	0.95	1.15	0.037	0.045	
с	0.33	0.65	0.013	0.026	
c2	1.17	1.40	0.046	0.055	
D	8.51	9.45	0.335	0.372	
D1	7.10	7.90	0.280	0.311	
E	9.80	10.31	0.386	0.406	
E1	6.50	8.60	0.256	0.339	
е	2.54		0.100		
e1	5.08		0.200		
N		2	2		
Н	14.61	15.88	0.575	0.625	
L	2.29	3.00	0.090	0.118	
L1	0.70	1.60	0.028	0.063	
L2	1.00	1.78	0.039	0.070	
F1	16.05	16.25	0.632	0.640	
F2	9.30	9.50	0.366	0.374	
F3	4.50	4.70	0.177	0.185	
F4	10.70	10.90	0.421	0.429	
F5	3.65	3.85	0.144	0.152	
F6	1.25	1.45	0.049	0.057	





F1

F3

FS

F6

F2

FOOTPRINT

F4





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